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FQA90N15

May 2014

N-Channel QFET[®] MOSFET 150 V, 90 A, 18 mΩ

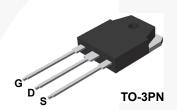
Features

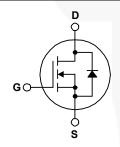
- $R_{DS(on)}$ = 18 $m\Omega$ (Max.) @ V_{GS} = 10 V, I_D = 45 A
- · Low Gate Charge (Typ. 220 nC)
- · Low Crss (Typ. 200 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Memperature Rating

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA90N15	Unit	
V_{DSS}	Drain-Source Voltage		150	V	
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		90 63.5	A A	
I _{DM}	Drain Current - Pulsed	(Note 1)	360	Α	
V _{GSS}	Gate-Source voltage		±25	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1400	mJ	
I _{AR}	Avalanche Current (N		90	Α	
E _{AR}	Repetitive Avalanche Energy (Note 1)		37.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns	
P _D	Power Dissipation (T _C = 25°C) - Derate Above 25°C		375 2.5	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQA90N15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA90N15	FQA90N15	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Parameter Conditions		Тур.	Max	Units
Off Charac	teristics			I		ı
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.15		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 150V, V _{GS} = 0V V _{DS} = 120V, T _C = 150°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25V, V _{DS} = 0V	-		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25V, V _{DS} = 0V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 45A		0.014	0.018	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 45A		68		S
Dynamic C	haracteristics				•	
C _{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$		6700	8700	pF
C _{oss}	Output Capacitance	f = 1.0MHz		1400	1800	pF
C _{rss}	Reverse Transfer Capacitance			200	260	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 75V, I _D = 90A		105	220	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$		760	1500	ns
t _{d(off)}	Turn-Off Delay Time			470	950	ns
t _f	Turn-Off Fall Time	(Note 4)		410	830	ns
Qg	Total Gate Charge	V _{DS} = 120V, I _D = 90A	/	220	285	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V	/	43		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	7-	110		nC
Drain-Sour	rce Diode Characteristics and Maximur	n Ratings	/	ı	Ż	
I _S	Maximum Continuous Drain-Source Diode Forward Current				90	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				360	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 90A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 90A		175		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		0.97		μС

NOTES

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 0.29 mH, I $_{AS}$ = 90 A, V $_{DD}$ = 25 V, R_{G} = 25 $\Omega,$ starting T $_{J}$ = 25°C.

 $^{3.}I_{SD} \leq 90$ A, di/dt ≤ 300 A/µs, $V_{DD} \leq BV_{DSS}$, starting T_J = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

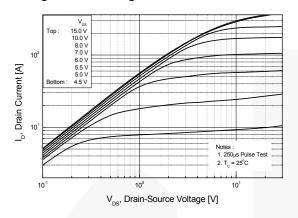


Figure 2. Transfer Characteristics

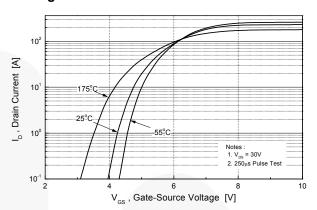


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

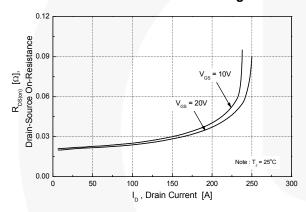


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

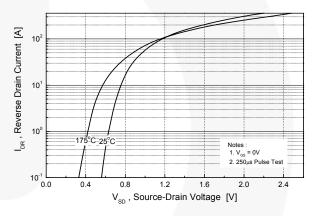


Figure 5. Capacitance Characteristics

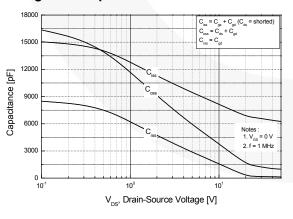
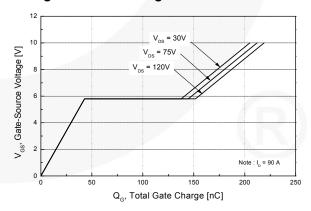


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

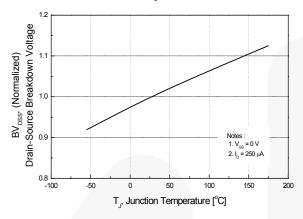


Figure 8. On-Resistance Variation vs. Temperature

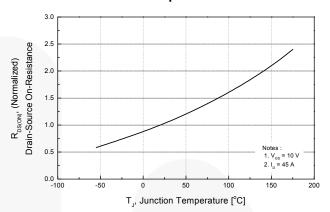


Figure 9. Maximum Safe Operating Area

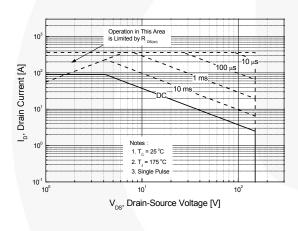


Figure 10. Maximum Drain Current vs. Case Temperature

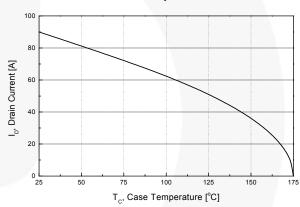
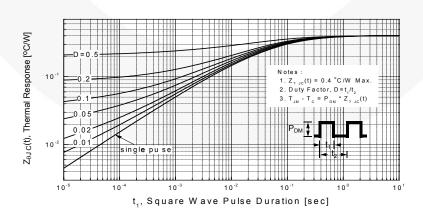


Figure 11. Transient Thermal Response Curve



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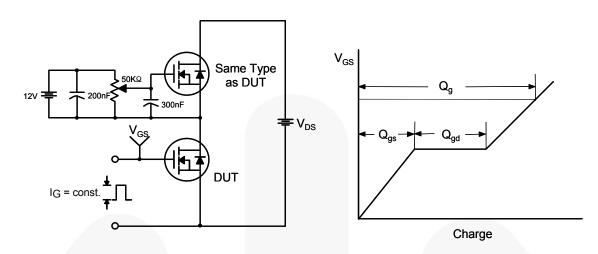


Figure 12. Gate Charge Test Circuit & Waveform

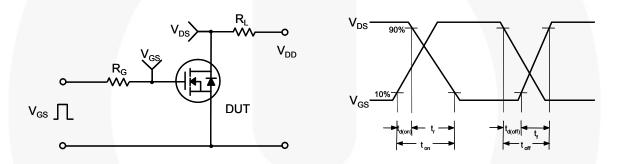


Figure 13. Resistive Switching Test Circuit & Waveforms

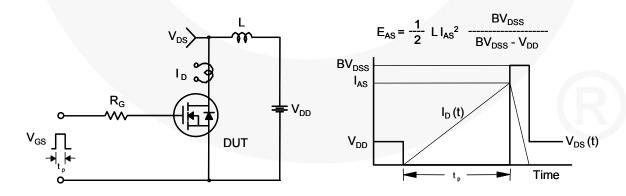


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

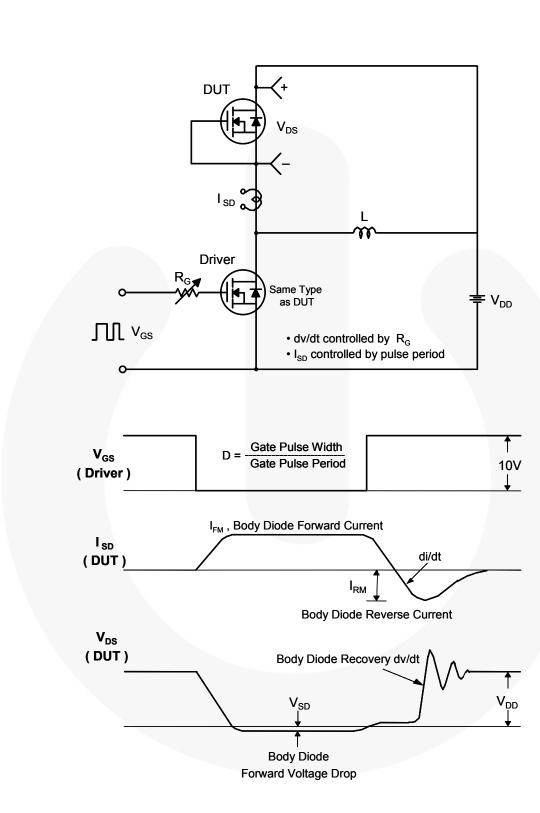
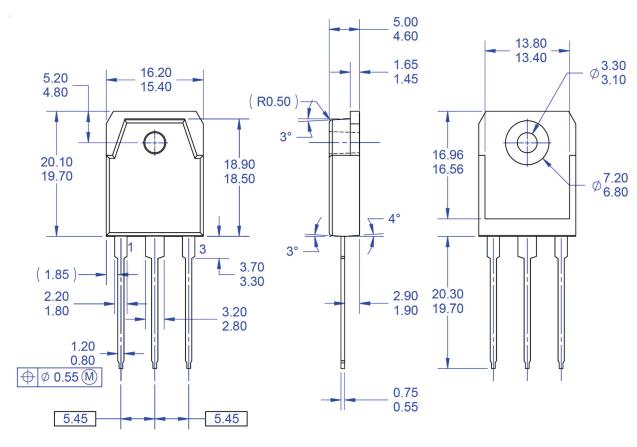
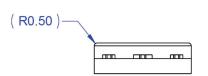


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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